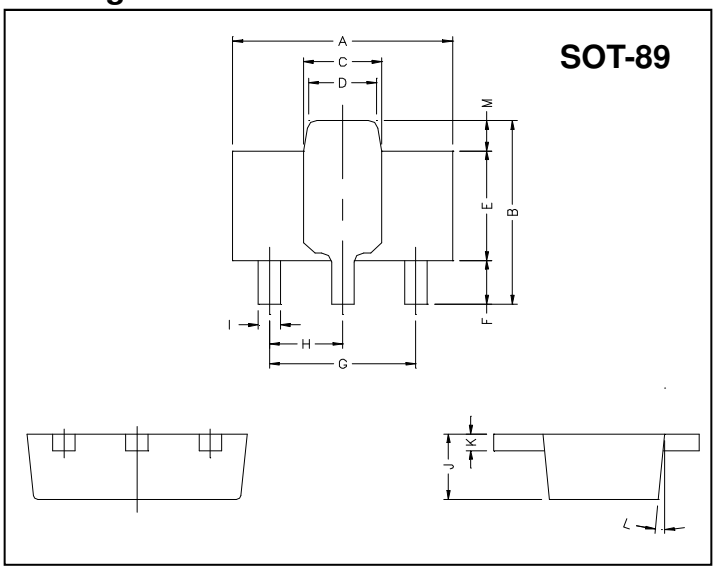
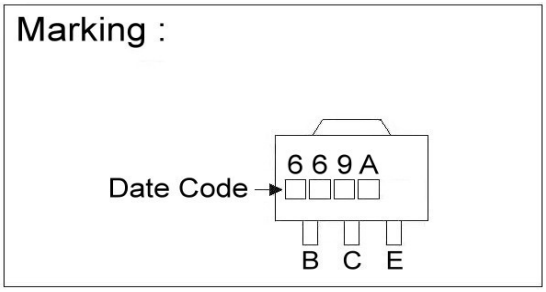
GM669A NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GM669A is designed for low frequency power amplifier complementary pair with GM649A.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00 REF.	
B	4.05	4.25	H	1.50 REF.	
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at T_A = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	5	V
Collect Current(DC)	I_C	1.5	A
Collect Current(Pulse)	I_C	3	A
Total Power Dissipation	P_D	1	W

Electrical Characteristics(T_A = 25℃)

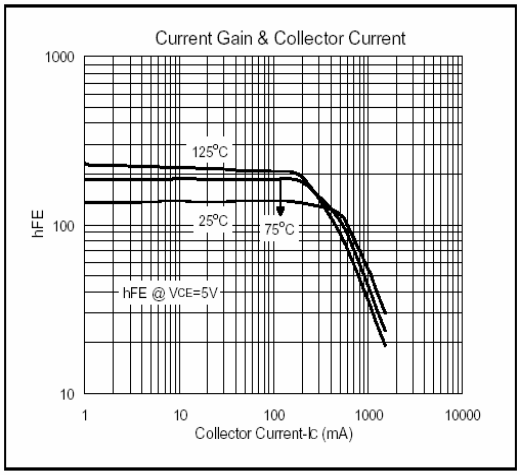
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	180	-	-	V	I_C=1mA, I_E=0
BV_{CEO}	160	-	-	V	I_C=10mA, I_B=0
BV_{EBO}	5	-	-	V	I_E=1mA, I_C=0
I_{CBO}	-	-	10	uA	V_{CB}=160V, I_E=0
*V_{CE}(sat)	-	-	1	V	I_C=600mA, I_B=50mA
*V_{BE}(on)	-	-	1.5	V	V_{CE}=5V, I_C=150mA
*h_{FE1}	60	-	200		V_{CE}=5V, I_C=150mA
*h_{FE2}	30	-	-		V_{CE}=5V, I_C=500mA
fT	-	140	-	MHz	V_{CE}=5V, I_C=10mA, f=100MHz
Cob	-	14	-	pF	VCB=10V, f=1MHz

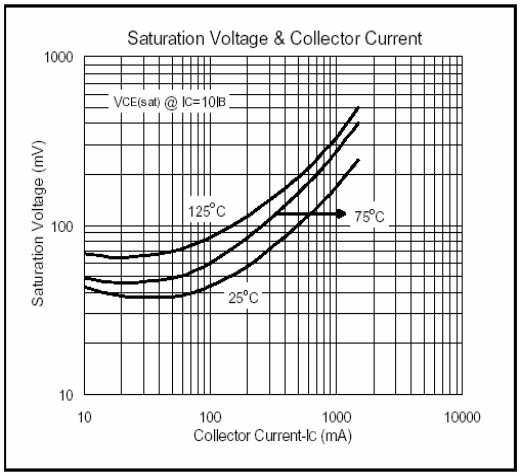
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

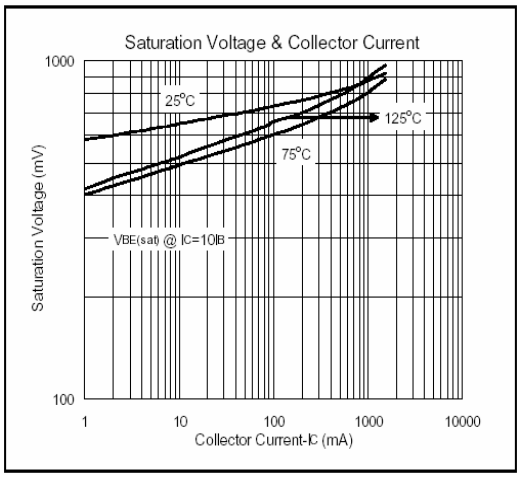
Classification Of h_{FE1}

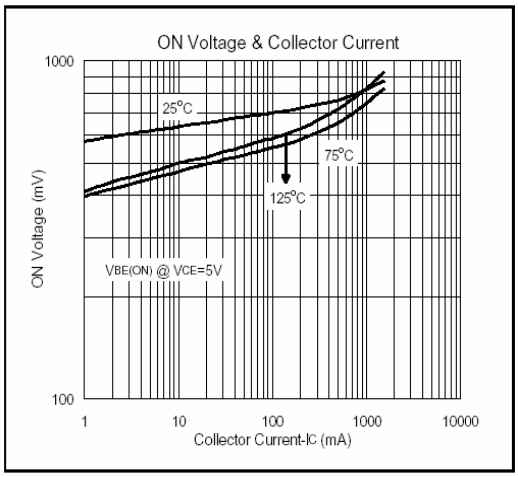
Rank	B	C
h_{FE1}	60 ~ 120	100 ~ 200

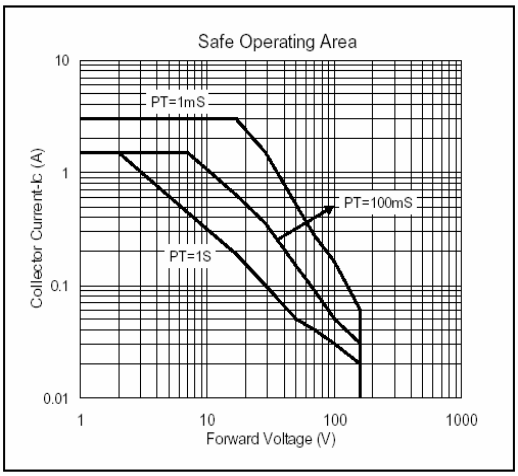
Characteristics Curve











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